DOCUMENT CHANGE REQUEST

DCR number 324	Changes required for: General	Originator: S JEFFERY
Date: 2007/02/21	Date sent: 2007/02/21	Organisation: ESA/ESTEC
Status: IMPLEMENTED		

Title:	Transistors High Power NPN, based on type BUX77		
Number:	5203/016	Issue:	1

Other documents affected:

Page:

Total re-write.

Paragraph:

Total re-write.

Original wording:

Proposed wording:

Total reformat of this specification (under Generic Specification No. 5000) as part of the ongoing conversion to the ESCC format. See below for summary of changes and attached Issue 2 Draft A of the Specification.

Note: known support for active procurement against this specification includes the following manufacturers:

STMICROELECTRONICS/F (Not ESCC qualified but are currently willing to support the procurement of Variants 03, 04, 05, 06 and 07)

Summary of changes to the current format, layout and content is as follows:

1. Rewording and restructure of various sections and paragraphs of the specification plus other editorial changes based on the layout and editorial content of other Detail Specifications already converted to ESCC format (e.g. changes described in DCR No. 203).

2. Deletion of any redundant paragraphs and information, e.g.: Mechanical Requirements.

3. Para. 1.7 High Temperature Test Precautions requirements moved to be a note in the Maximum Ratings table.

4. Deletion of obsolete lead finishes D2, D3 and D4 / Variants 01 and 02 from the available range (not supported by STMicroelectronics).

5. Figure 1(a) Parameter Derating Information moved to be a note in the Maximum Ratings table.

6. Figure 1(b) Forward Bias Safe Operating Area (Continuous DC) amended and moved to be a note in the Maximum

DCR number 324	Changes required for: General	Originator: S JEFFERY
Date: 2007/02/21	Date sent: 2007/02/21	Organisation: ESA/ESTEC
Status: IMPLEMENTED		

Ratings table.

7. Para. 4.3.2 Weight requirements moved to Component Type Variants table.

8. Figure 2 re-named â..Physical Dimensions and Terminal Identificationâ.; Figure 2(a) amended to reflect the TO-66 package currently supplied; Figure 2(b) amended to reflect the TO-257 package currently supplied. Consolidated notes added.

9. Para. 4.4.1 Case requirements corrected to reflect TO-66 and TO-257 metal flange mount packages.

10. Para. 4.4.2 Lead Material and Finish replaced by a reference to the Component Type Variants Para.

11. Para. 4.5.1 Required part marking corrected: Lead Identification removed, ESCC qualified components symbol added and warning sign for Beryllium Oxide (TO-257 only) added.

12. Delete requirement for marking of the test level letter from the ESCC Component Number as per latest ESCC No. 21700.

13. Para. 4.7.6 Verification of Safe Operating Area: Para. revised and Test Method corrected (was 3052, now 3051).

14. Table 2, Characteristic â..D.C. Forward Current Transfer Ratioâ. has been changed to â..Forward-Current Transfer Ratioâ..

15. Table 2, Characteristic â..A.C. Forward Current Transfer Ratioâ. has been changed to â..High Frequency Small Signal Current Gainâ.. Test Method corrected (was 3206, now 3306).

16. Table 2: Replace LTPD7 sampling for AC parameters tests (designated by â..Note 2â.) with an equivalent fixed sample of 32 components with 0 failures (or 100%).

17. Table 2 and Figure 4: The Switching Times characteristics have been amended to reflect the new format.

18. Table 3, Characteristic â..D.C. Forward Current Transfer Ratio 4â. has been changed to â..Forward-Current Transfer Ratio 4â..

19. Table 3 (High and Low Temperature Electrical Measurements): 100% inspection has been replaced by a sample of 5 components with 0 failures, or 100%, in line with the new Generic 5000 Issue 3.

20. Table 3, Test Conditions: standard tolerances have been added to the specified Tamb.

21. Table 4: Absolute limits have been added for information.

22. Tables 4 and 6, Characteristic â..D.C. Forward Current Transfer Ratio 2â. has been changed to â..Forward-Current Transfer Ratio 2â..

DOCUMENT CHANGE REQUEST

DCR number 324	Changes required for: General	Originator: S JEFFERY
Date: 2007/02/21	Date sent: 2007/02/21	Organisation: ESA/ESTEC
Status: IMPLEMENTED		

23. Tables 2, 3 and 4 â.. Test Conditions column: addition of Test, or Bias, Conditions for referenced MIL-STD-750 Test Methods as and where applicable.

24. Appendix A for STMicroelectronics added to introduce a note about wafer level pilot lot testing in that AC characteristics during screening may be guaranteed but not tested. Note STMicroelectronics is an ESCC QPL listed manufacturer; this amendment is considered technically acceptable on this basis.

Justification:

(see also change details for each item above)

1. Part of the ongoing activity of conversion of cover-sheeted ESA/SCC Specifications to the ESCC format.

2. To make the format and presentation consistent with the various other ESCC Detail Specifications already converted to ESCC format.

3. To make the content consistent with ESCC Generic Specification No. 5000 Issue 3.

4. To incorporate specific deviations requested by manufacturer STMicroelectronics within Appendix A which are considered technically acceptable (see also DCR No. 187).

5. Update manufacturerâ..s current product availability.

6. To make corrections to technical errors in the previous issue.

7. Standardisation of the TO-66 and TO-257 packages in all applicable ESCC Detail Specifications.

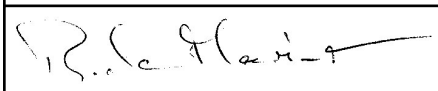
Attachments:

5203016_editorials_prior_to_publishing.pdf, 5203016_Issue_2_-_Draft_A.pdf, null

Modifications:

N/A

Approval signature:



Date signed:

2007-02-21

TRANSISTORS, HIGH POWER, NPN

BASED ON TYPE BUX77

ESCC Detail Specification No. 5203/016

Issue 2 - Draft A	February 2007

Document Custodian: European Space Agency - see https://escies.org

LEGAL DISCLAIMER AND COPYRIGHT

European Space Agency, Copyright © 2007. All rights reserved.
The European Space Agency disclaims any liability or responsibility, to any person or entity, with respect to any loss or damage caused, or alleged to be caused, directly or indirectly by the use and application of this ESCC publication.
This publication, without the prior permission of the European Space Agency and provided that it is not used for a commercial purpose, may be:
– copied in whole, in any medium, without alteration or modification.
– copied in part, in any medium, provided that the ESCC document identification, comprising the ESCC symbol, document number and document issue, is removed.

DOCUMENTATION CHANGE NOTICE

(Refer to https://escies.org for ESCC DCR content)

DCR No.	CHANGE DESCRIPTION
187, TBD	Specification up issued to incorporate editorial and technical changes per DCR.

TABLE OF CONTENTS

1.	**GENERAL**	**5**
1.1	Scope	5
1.2	Applicable Documents	5
1.3	Terms, Definitions, Abbreviations, Symbols and Units	5
1.4	The ESCC Component Number and Component Type Variants	5
1.4.1	The ESCC Component Number	5
1.4.2	Component Type Variants	5
1.5	Maximum Ratings	5
1.6	Handling Precautions	7
1.7	Physical Dimensions and Terminal Identification	7
1.7.1	Metal Flange Mount Package (TO-66) - 2 lead	8
1.7.2	Metal Flange Mount Package (TO-257) - 3 lead	9
1.7.3	Consolidated Notes	9
1.8	Functional Diagram	10
1.9	Materials and Finishes	10
2.	**REQUIREMENTS**	**10**
2.1	General	10
2.1.1	Deviations from the Generic Specification	10
2.2	Marking	11
2.3	Terminal Strength	11
2.4	Verification of Safe Operating Area	11
2.5	Electrical Measurements at Room, High and Low Temperatures	11
2.5.1	Room Temperature Electrical Measurements	11
2.5.2	High and Low Temperatures Electrical Measurements	13
2.6	Parameter Drift Values	14
2.7	Intermediate and End-Point Electrical Measurements	14
2.8	Power Burn-in Conditions	14
2.9	Operating Life Conditions	15
APPENDIX ‘A’		16

1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

(a) ESCC Generic Specification No. 5000

(b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 520301603

- Detail Specification Reference: 5203016
- Component Type Variant Number: 03 (as required)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead Material and Finish	Weight max g
03	BUX77	TO-66	F9	6.4
04	BUX77	TO-66	F2	6.4
05	BUX77	TO-66	F3 or F4	6.4
06	BUX77	TO-257	H2	5
07	BUX77	TO-257	H4	5

The lead material and finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage	V_{CBO}	100	V	Over T_{op}
Collector-Emitter Voltage	V_{CEO}	80	V	Over T_{op} Note 4
Emitter-Base Voltage	V_{EBO}	6	V	Over T_{op}
Collector Current	I_C	5	A	Continuous Note 4
Base Current	I_B	800	mA	Continuous
Power Dissipation For TO-66 For TO-257	P_{tot}	 40 35	W	At $T_{case} \leq +25^{\circ}C$ Note 1
Operating Temperature Range	T_{op}	-65 to +200	^{o}C	Note 2
Storage Temperature Range	T_{stg}	-65 to +200	^{o}C	Note 2
Soldering Temperature	T_{sol}	+260	^{o}C	Note 3
Thermal Resistance Junction to Case For TO-66 For TO-257	$R_{th(j-c)}$	 4.4 5	$^{o}C/W$	

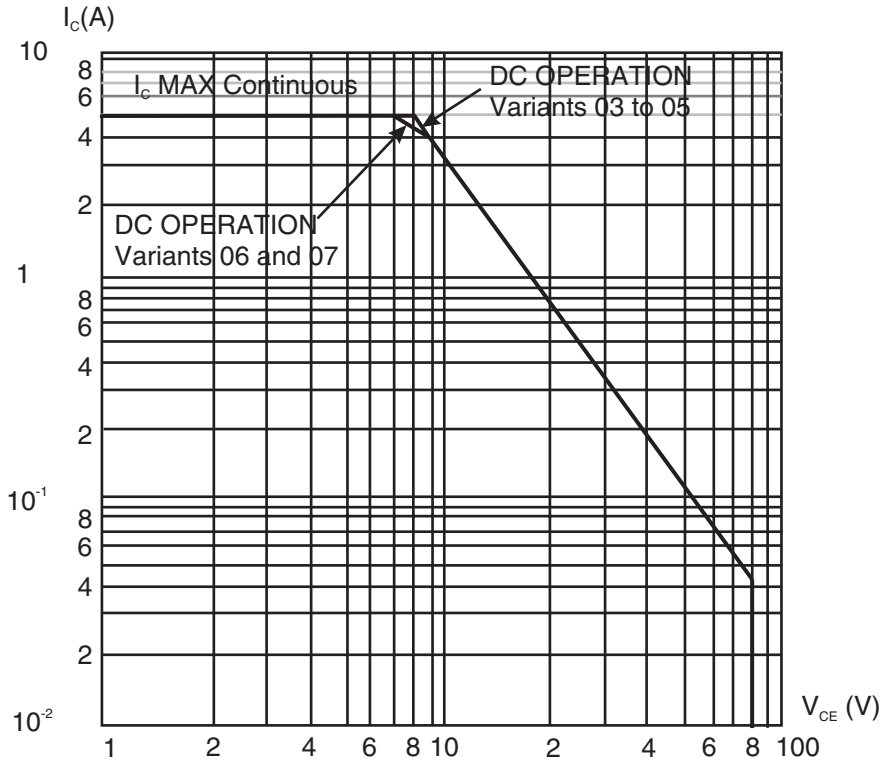
NOTES:

1. For $T_{case} > +25^{o}C$, derate linearly to 0W at $+200^{o}C$.
2. For Variants with tin-lead plating or hot solder dip lead finish all testing performed at $T_{amb} > +125^{o}C$ shall be carried out in a 100% inert atmosphere.
3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the

same lead shall not be resoldered until 3 minutes have elapsed.

4. Safe Operation Area applies as follows:

Maximum Safe Operating Area Graph



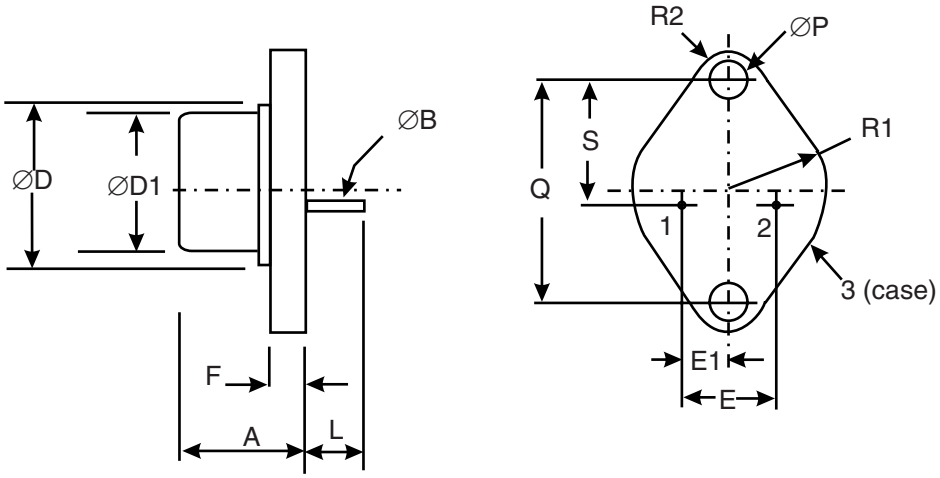
1.6 HANDLING PRECAUTIONS

The TO-257 package contains Beryllium Oxide (BeO) and therefore it must not be ground, machined, sandblasted or subjected to any mechanical operation which will produce dust. The case must not be subjected to any chemical process (e.g. etching) which will produce fumes.

1.7 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

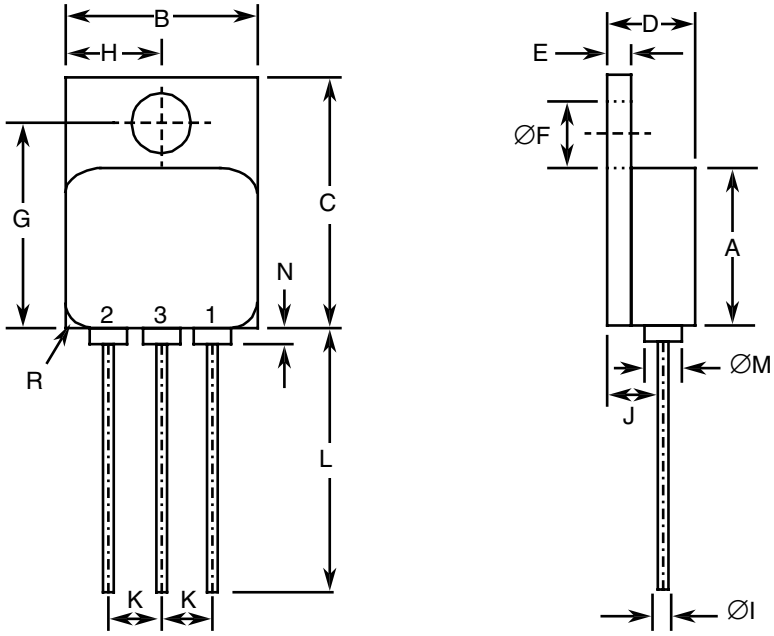
Consolidated Notes are given following the case drawings and dimensions.

1.7.1 Metal Flange Mount Package (TO-66) - 2 lead



Symbols	Dimensions mm		Notes
	Min	Max	
A	6.35	8.64	
ØB	0.71	0.86	2
ØD	-	15.74	
ØD1	11.94	12.7	
E	4.83	5.34	
E1	2.36	2.72	
F	1.27	1.91	
L	9.14	-	
ØP	3.61	3.86	3
Q	24.33	24.43	
R1	-	8.89	
R2	2.92	3.68	
S	14.48	14.99	

1.7.2 Metal Flange Mount Package (TO-257) - 3 lead



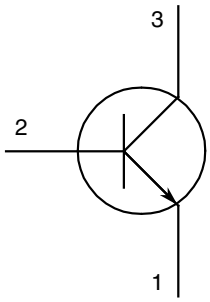
Symbols	Dimensions mm		Notes
	Min	Max	
A	10.41	10.67	
B	10.41	10.67	
C	16.51	16.76	
D	4.7	5.33	
E	0.89	1.14	
ØF	3.56	3.81	
G	13.39	13.64	
H	5.13	5.38	
ØI	0.64	0.89	2
J	2.92	3.16	
K	2.41	2.67	
L	15.24	16.51	
ØM	2.29 Typical		2
N	-	0.71	2
R	1.65 Typical		4

1.7.3 Consolidated Notes

1. Terminal identification is specified by the component's geometry where Lead 1 = emitter, Lead 2 = base and Lead 3 (TO-257) or Case (TO-66) = collector.
2. Applies to all leads.
3. Applies to both mounting holes.

4. Radius of body corner, 4 places.

1.8 FUNCTIONAL DIAGRAM



1. Emitter.
2. Base.
3. Collector.

NOTES:
1. For TO-66, the collector is internally connected to the case.
2. For TO-257, the case is not connected to any lead.

1.9 MATERIALS AND FINISHES

Materials and finishes shall be as follows:

a) Case
For the metal flange mount (TO-66) package the case shall be hermetically sealed and have a metal body.
For the metal flange mount (TO-257) package the case shall be hermetically sealed and have a metal body. The leads pass through ceramic eyelets brazed into the frame and the lid shall be welded.

b) Leads
As specified in Component Type Variants.

2. REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.
Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

(a) Deviation from Screening Tests - Chart F3
High Temperature Reverse Bias Burn-in and the subsequent Final Measurements for HTRB shall be omitted.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.
The information to be marked on the component shall be:
(a) The ESCC qualified components symbol (for ESCC qualified components only).
(b) The ESCC Component Number.
(c) Traceability information.
(d) Warning sign for Beryllium Oxide (TO-257 only).

2.3 TERMINAL STRENGTH

The test conditions for terminal strength, tested as specified in the ESCC Generic Specification, shall be as follows:
Test Condition A, tension, with an applied force of 10N for a duration of 10s.

2.4 VERIFICATION OF SAFE OPERATING AREA

The Safe Operating Area shall be verified as specified in the ESCC Generic Specification and Maximum Ratings herein. The test conditions shall be:
Test Method = MIL-STD-750, Method 3051, Continuous DC
T_{case} = +25°C
V_{CE}= 12V
I_C= 2A
Operating Time ≤ 100ms

2.5 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

Electrical measurements shall be performed at room, high and low temperatures.

2.5.1 Room Temperature Electrical Measurements

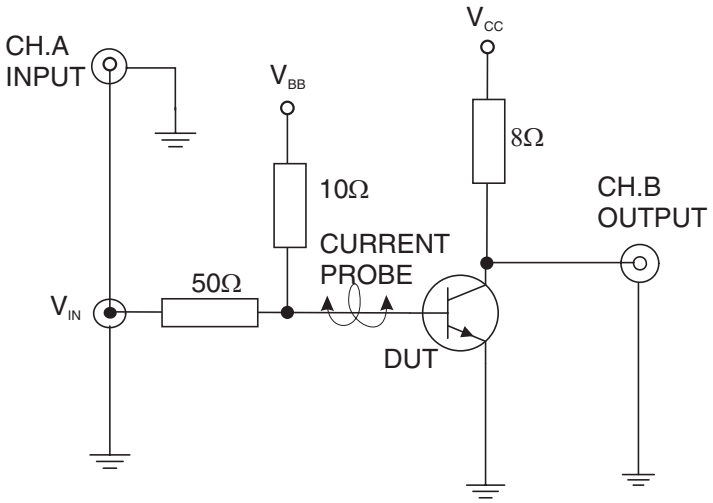
The measurements shall be performed at T_{amb}=+22 ±3°C.

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	3011	I_C =50mA Bias condition D Note 1	80	-	V
	$V_{(BR)CES}$	3011	I_C =2mA Bias condition C	100	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	3026	I_E =1mA Bias condition D	6	-	V
Collector-Emitter Cut-off Current	I_{CEO}	3041	V_{CE} = 60V Bias condition D	-	10	µA
Collector-Base Cut-off Current	I_{CBO}	3036	V_{CB} = 80V Bias condition D	-	500	nA
Emitter-Base Cut-off Current	I_{EBO}	3061	V_{EB}=4V Bias condition D	-	500	nA

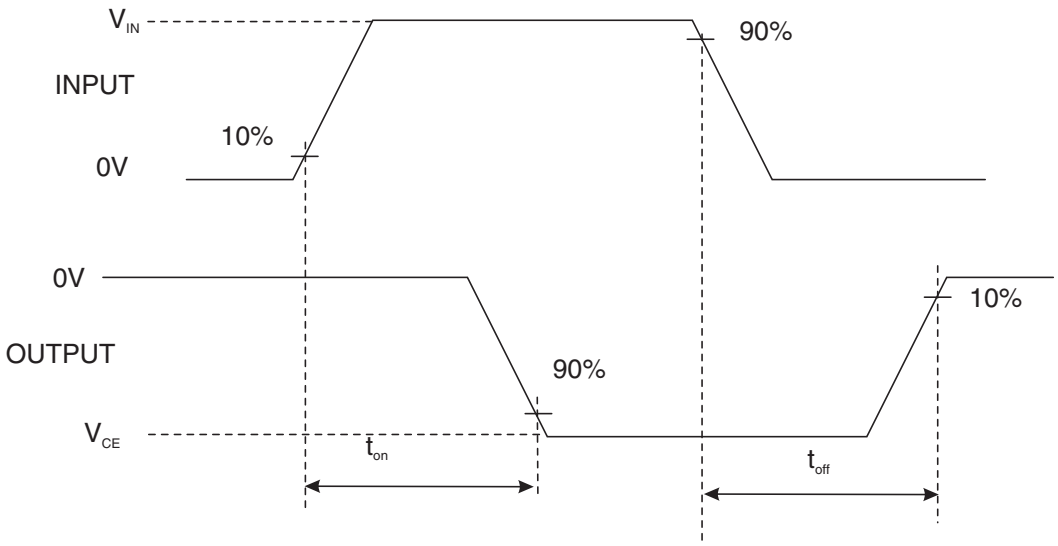
Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Forward-Current Transfer Ratio	h_{FE1}	3076	V_{CE}=5V ; I_C = 500mA Note 1	70	-	-
	h_{FE2}	3076	V_{CE}=5V ; I_C = 2A Note 1	50	200	-
	h_{FE3}	3076	V_{CE}=5V ; I_C = 5A Note 1	30	-	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	3071	I_C=5A I_B=500mA Note 1	-	1	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	3066	I_C=5A I_B=500mA Test condition A Note 1	-	1.3	V
High Frequency Small Signal Current Gain	h_{fe}	3306	V_{CE}=5V, I_C=500mA f=20MHz Note 2	2.5	-	-
Turn-on Time	t_{on}	-	I_C=5A, I_{B1}=500mA I_{B2}=-500mA V_{CC}=40V V_{BB}=-4V V_{IN}≈51V Notes 2, 3	-	300	ns
Turn-off Time	t_{off}	-	I_C=5A, I_{B1}=500mA I_{B2}=-500mA V_{CC}=40V V_{BB}=-4V V_{IN}≈51V Notes 2, 3	-	700	ns

NOTES:

1. Pulsed measurement: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
2. For AC characteristics read and record measurements shall be performed on a sample of 32 components with 0 failures allowed. Alternatively a 100% inspection may be performed.
3. t_{on} and t_{off} shall be measured using the following test circuit. The input waveform shall be supplied by a pulse generator with the following characteristics: t_r ≤ 20ns, Pulse Width = 10µs, Duty Cycle = 1%. The sampling oscilloscope for CH.A and CH.B shall have the characteristics Z_{IN} ≥ 100kΩ, C_{IN} ≤ 12pF and t_f ≤ 5ns. Adjustment of V_{IN} shall be made with a suitable current probe to achieve the specified I_{B1} and I_{B2} test conditions, where I_{B1} is the on-state base current and I_{B2} is the post off-state base current.



VOLTAGE WAVEFORMS



2.5.2 High and Low Temperatures Electrical Measurements

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Collector-Base Cut-off Current	I_{CBO}	3036	T_{amb}=+150(+0 -5)°C V_{CB} = 80V Bias condition D	-	150	µA
Forward-Current Transfer Ratio 4	h_{FE4}	3076	T_{amb}=-55(+5 -0)°C V_{CE}=5V ; I_C =1A Note 2	25	-	-

NOTES:
1. Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.
2. Pulsed measurement: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

2.6 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at T_{amb}=+22 ±3°C.
The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.
The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Emitter-Base Cut-off Current	I_{EBO}	±100	-	500	nA
Forward-Current Transfer Ratio 2	h_{FE2}	±25%	50	200	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	±100	-	1000	mV

2.7 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at T_{amb}=+22 ±3°C.
The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.
The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits		Units
		Min	Max	
Collector-Emitter Cut-off Current	I_{CEO}	-	10	µA
Forward-Current Transfer Ratio 2	h_{FE2}	50	200	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-	1	V

2.8 POWER BURN-IN CONDITIONS

Characteristics	Symbols	Conditions	Units
Case Temperature	T_{case}	+100 (+0 -5) (1)	°C
Power Dissipation	P_{tot}	As per Maximum Ratings P_{tot} derated at the specified T_{case}	W
Collector-Emitter Voltage	V_{CE}	10	V

NOTES:
1. No heat sink nor forced air directly on the device shall be permitted.

2.9 OPERATING LIFE CONDITIONS

The conditions shall be as specified for Power Burn-in.

APPENDIX 'A'

AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Deviations from Room Temperature Electrical Measurements	All AC characteristics (Room Temperature Electrical Measurement Note 2) may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes AC characteristic measurements per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.
Deviations from High and Low Temperatures Electrical Measurements	All characteristics specified may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes characteristic measurements at high and low temperatures per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.

DOCUMENTATION CHANGE NOTICE

(Refer to https://escies.org for ESCC DCR content)

DCR No.	CHANGE DESCRIPTION
187,	Specification up issued to incorporate editorial and technical changes per DCR.

324

1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

(a) ESCC Generic Specification No. 5000
(b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:
Example: 520301603

- Detail Specification Reference: 5203016
- Component Type Variant Number: 03 (as required)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead Material and Finish	Weight max g
03	BUX77	TO-66	F9	6.4
04	BUX77	TO-66	F2	6.4
05	BUX77	TO-66	F3 or F4	6.4
06	BUX77	TO-257	H2	5
07	BUX77	TO-257	H4	5

The lead material and finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

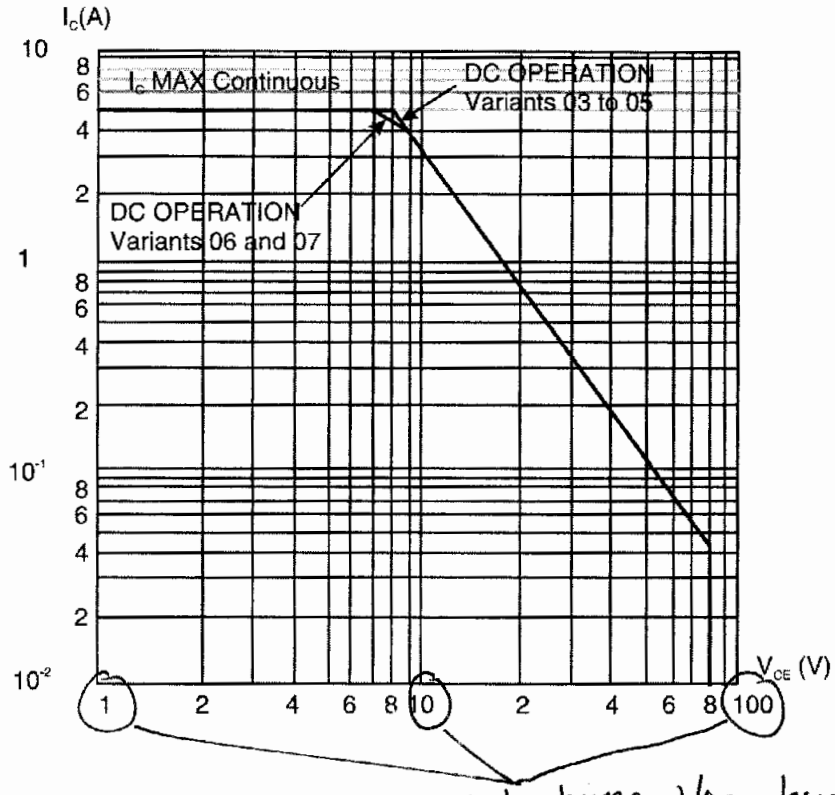
1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.
Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

same lead shall not be resoldered until 3 minutes have elapsed.

4. Safe Operation Area applies as follows:

Maximum Safe Operating Area Graph



make lower &/or larger than the other numbers (eg: 6 8 100)

1.6 HANDLING PRECAUTIONS

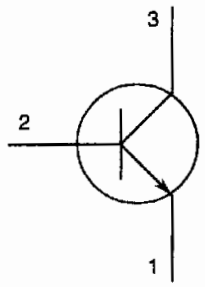
The TO-257 package contains Beryllium Oxide (BeO) and therefore it must not be ground, machined, sandblasted or subjected to any mechanical operation which will produce dust. The case must not be subjected to any chemical process (e.g. etching) which will produce fumes.

1.7 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

Consolidated Notes are given following the case drawings and dimensions.

4. Radius of body corner, 4 places.

1.8 FUNCTIONAL DIAGRAM



1. Emitter.
2. Base.
3. Collector.

NOTES:
1. For TO-66, the collector is internally connected to the case.
2. For TO-257, the case is not connected to any lead.

1.9 MATERIALS AND FINISHES

Materials and finishes shall be as follows:

a) Case
For the metal flange mount (TO-66) package the case shall be hermetically sealed and have a metal body with hard glass seals.
For the metal flange mount (TO-257) package the case shall be hermetically sealed and have a metal body. The leads pass through ceramic eyelets brazed into the frame and the lid shall be welded.

b) Leads/Terminals
As specified in Component Type Variants.

2. REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.
Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

(a) Deviation from Screening Tests - Chart F3
High Temperature Reverse Bias Burn-in and the subsequent Final Measurements for HTRB shall be omitted.